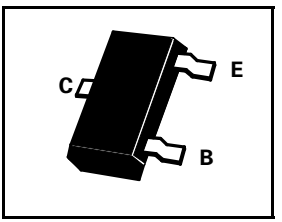
SOT23 PNP SILICON PLANAR HIGH SPEED TRANSISTOR

BSS65

ISSUE 2 - SEPTEMBER 1995 ✪

PARTMARKING DETAIL — BSS65 - L1
BSS65R - L5



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-12	V
Collector-Emitter Voltage	V_{CEO}	-12	V
Emitter-Base Voltage	V_{EBO}	-4	V
Peak Pulse Current	I_{CM}	-200	mA
Continuous Collector Current	I_C	-100	mA
Base Current	I_C	-50	mA
Power Dissipation at T_{amb}=25°C	P_{TOT}	330	mW
Operating and Storage Temperature Range	t_j:t_{stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
BreakdownVoltages	$V_{(BR)CEO}$	-12			V	I_C=-10mA
	$V_{(BR)CBO}$	-12			V	I_C=-10μA *
	$V_{(BR)EBO}$	-4			V	I_E=-10μA
Cut-Off Currents	I_{CBO}			-100	nA	V_{CB}=-6V, I_E=0
	I_{EBO}			-100	nA	V_{EB}=-4V, I_C=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.15 -0.25	V V	I_C=-10mA, I_B=-1mA I_C=-30mA, I_B=-3mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-0.75 -0.82		-0.98 -1.20	V V	I_C=-10mA, I_B=-1mA I_C=-30mA, I_B=-3mA
Static Forward Current Transfer Ratio	h_{FE}	30 40		 150		I_C=-10mA, V_{CE}=-0.3V I_C=-30mA, V_{CE}=-0.5V
Transition Frequency	f_T	400			MHz	I_C=-30mA, V_{CE}=-10V, f=100MHz
Collector-Base Capacitance	C_{obo}			6	pF	V_{CB}=-5V, I_E=0, f=1MHz
Emitter Base Capacitance	C_{ebo}			6	pF	V_{EB}=-0.5V, I_C=0, f=1MHz
Switching Times Turn-On Time Turn-Off Time	 t_{on} t_{off}		 23 34	 60 90	 nS nS	 I_C=-30mA I_{B1} = -I_{B2}= -1.5mA V_{CC}=-10V